

Jian Tang

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/7814843/publications.pdf>

Version: 2024-02-01

43
papers

2,283
citations

304602

22
h-index

289141

40
g-index

46
all docs

46
docs citations

46
times ranked

3281
citing authors

#	ARTICLE	IF	CITATIONS
1	Ultra-low friction and edge-pinning effect in large-lattice-mismatch van der Waals heterostructures. Nature Materials, 2022, 21, 47-53.	13.3	110
2	Interlayer exciton complexes in bilayer MoS_2 . Physical Review B, 2022, 105, .	11.1	10
3	Gate-tunable large-scale flexible monolayer MoS_2 devices for photodetectors and optoelectronic synapses. Nano Research, 2022, 15, 5418-5424.	5.8	48
4	Enhanced critical field and anomalous metallic state in two-dimensional centrosymmetric WTe_2 . Physical Review B, 2022, 105, .	1.1	6
5	Layer-by-layer epitaxy of multi-layer MoS_2 wafers. National Science Review, 2022, 9, .	4.6	41
6	Hot-Pressed Two-Dimensional Amorphous Metals and Their Electronic Properties. Crystals, 2022, 12, 616.	1.0	0
7	Highly Stretchable MoS_2 -Based Transistors with Opto-Synaptic Functionalities. Advanced Electronic Materials, 2022, 8, .	2.6	8
8	Rail-to-Rail MoS_2 Inverters. ACS Applied Electronic Materials, 2022, 4, 2636-2640.	2.0	2
9	Isospin competitions and valley polarized correlated insulators in twisted double bilayer graphene. Nature Communications, 2022, 13, .	5.8	20
10	Temperature-linear resistivity in twisted double bilayer graphene. Physical Review B, 2022, 106, .	1.1	8
11	A Reliable All-2D Materials Artificial Synapse for High Energy-Efficient Neuromorphic Computing. Advanced Functional Materials, 2021, 31, 2011083.	7.8	53
12	Wafer-Scale Oxygen-Doped MoS_2 Monolayer. Small Methods, 2021, 5, e2100091.	4.6	30
13	Emergence of Chern Insulating States in Non-Magic Angle Twisted Bilayer Graphene. Chinese Physics Letters, 2021, 38, 047301.	1.3	20
14	Exchange bias and spin-orbit torque in the Fe_3GeTe_2 -based heterostructures prepared by vacuum exfoliation approach. Applied Physics Letters, 2021, 118, .	1.5	27
15	Inside Back Cover: Wafer-Scale Oxygen-Doped MoS_2 Monolayer (Small Methods 6/2021). Small Methods, 2021, 5, 2170026.	4.6	0
16	Artificial Synapses: A Reliable All-2D Materials Artificial Synapse for High Energy-Efficient Neuromorphic Computing (Adv. Funct. Mater. 27/2021). Advanced Functional Materials, 2021, 31, 2170197.	7.8	2
17	Skin-Inspired High-Performance Active-Matrix Circuitry for Multimodal User-Interaction. Advanced Functional Materials, 2021, 31, 2105480.	7.8	14
18	Twist-Angle-Dependent Ultrafast Charge Transfer in MoS_2 -Graphene van der Waals Heterostructures. Nano Letters, 2021, 21, 8051-8057.	4.5	30

#	ARTICLE	IF	CITATIONS
19	Vertical Integration of 2D Building Blocks for All-2D Electronics. <i>Advanced Electronic Materials</i> , 2020, 6, 2000550.	2.6	20
20	Observation of logarithmic Kohn anomaly in monolayer graphene. <i>Physical Review B</i> , 2020, 102, .	1.1	6
21	In Situ Oxygen Doping of Monolayer MoS ₂ for Novel Electronics. <i>Small</i> , 2020, 16, e2004276.	5.2	54
22	Wafer-Scale Highly Oriented Monolayer MoS ₂ with Large Domain Sizes. <i>Nano Letters</i> , 2020, 20, 7193-7199.	4.5	160
23	Employing defected monolayer MoS ₂ as charge storage materials. <i>Nanotechnology</i> , 2020, 31, 235710.	1.3	0
24	Correlated states in twisted double bilayer graphene. <i>Nature Physics</i> , 2020, 16, 520-525.	6.5	374
25	High-order minibands and interband Landau level reconstruction in graphene moiré superlattices. <i>Physical Review B</i> , 2020, 102, .	1.1	7
26	Artificial Synapse Based on van der Waals Heterostructures with Tunable Synaptic Functions for Neuromorphic Computing. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 11945-11954.	4.0	75
27	Precise control of the interlayer twist angle in large scale MoS ₂ homostructures. <i>Nature Communications</i> , 2020, 11, 2153.	5.8	142
28	Scratching lithography for wafer-scale MoS ₂ monolayers. <i>2D Materials</i> , 2020, 7, 045028.	2.0	11
29	Lattice Dynamics, Phonon Chirality, and Spin-Phonon Coupling in 2D Itinerant Ferromagnet Fe ₃ GeTe ₂ . <i>Advanced Functional Materials</i> , 2019, 29, 1904734.	7.8	70
30	Current-driven magnetization switching in a van der Waals ferromagnet Fe ₃ GeTe ₂ . <i>Science Advances</i> , 2019, 5, eaaw8904.	4.7	239
31	Atomic Layer Deposition: Atomic Layer Deposition of Al ₂ O ₃ Directly on 2D Materials for High-Performance Electronics (Adv. Mater. Interfaces 10/2019). <i>Advanced Materials Interfaces</i> , 2019, 6, 1970065.	1.9	2
32	Atomic Layer Deposition of Al ₂ O ₃ Directly on 2D Materials for High-Performance Electronics. <i>Advanced Materials Interfaces</i> , 2019, 6, 1802055.	1.9	25
33	Nonvolatile Memory: New Floating Gate Memory with Excellent Retention Characteristics (Adv.) Tj ETQq1 1 0.784314 rgBT /Qoverlock 10	2.6	8
34	Electronic synapses based on ultrathin quasi-two-dimensional gallium oxide memristor. <i>Chinese Physics B</i> , 2019, 28, 017304.	0.7	16
35	2D proximate quantum spin liquid state in atomic-thin RuCl_3 . <i>2D Materials</i> , 2019, 6, 015014.	2.0	28
36	New Floating Gate Memory with Excellent Retention Characteristics. <i>Advanced Electronic Materials</i> , 2019, 5, 1800726.	2.6	48

#	ARTICLE	IF	CITATIONS
37	Giant Valley Coherence at Room Temperature in 3R WS ₂ with Broken Inversion Symmetry. Research, 2019, 2019, 6494565.	2.8	17
38	Twist angle-dependent conductivities across MoS ₂ /graphene heterojunctions. Nature Communications, 2018, 9, 4068.	5.8	90
39	Strongly enhanced exciton-phonon coupling in two-dimensional WS ₂ . Physical Review B, 2018, 97, .	1.1	30
40	Graphene-Contacted Ultrashort Channel Monolayer MoS ₂ Transistors. Advanced Materials, 2017, 29, 1702522.	11.1	218
41	Thermally Induced Graphene Rotation on Hexagonal Boron Nitride. Physical Review Letters, 2016, 116, 126101.	2.9	142
42	Adjustable plasmonic optical properties of hollow gold nanospheres monolayers and LSPR-dependent surface-enhanced Raman scattering of hollow gold nanosphere/graphene oxide hybrids. RSC Advances, 2015, 5, 42653-42662.	1.7	15
43	Sandwich-structured Ag/graphene/Au hybrid for surface-enhanced Raman scattering. Electrochimica Acta, 2014, 119, 43-48.	2.6	54